64K x 18 Bit BurstRAM Synchronous Fast Static RAM

With Burst Counter and Self-Timed Write

The MCM67B618B is a 1,179,648—bit synchronous fast static random access memory designed to provide a burstable, high–performance, secondary cache for the i486™ and Pentium® microprocessors. The MCM67B618B (organized as 65,536 words by 18 bits) is fabricated using Motorola's high–performance silicon–gate BiCMOS technology. The device integrates input registers, a 2–bit counter, high speed SRAM, and high drive capability outputs onto a single monolithic circuit for reduced parts count implementation of cache data RAM applications. Synchronous design allows precise cycle control with the use of an external clock (K). BiCMOS circuitry reduces the overall power consumption of the integrated functions for greater reliability.

Addresses (A0 – A15), data inputs (D0 – D17), and all control signals except output enable (\overline{G}) are clock (K) controlled through positive–edge–triggered noninverting registers.

Bursts can be initiated with either address status processor (\overline{ADSP}) or address status cache controller (\overline{ADSC}) input pins. Subsequent burst addresses can be generated internally by the MCM67B618B (burst sequence imitates that of the i486 and Pentium) and controlled by the burst address advance (\overline{ADV}) input pin. The following pages provide more detailed information on burst controls.

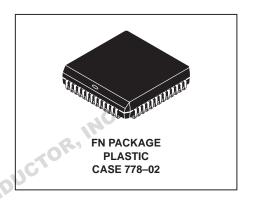
Write cycles are internally self–timed and are initiated by the rising edge of the clock (K) input. This feature eliminates complex off–chip write pulse generation and provides increased flexibility for incoming signals.

Dual write enables (\overline{LW} and \overline{UW}) are provided to allow individually writeable bytes. \overline{LW} controls DQ0 – DQ8 (the lower bits), while \overline{UW} controls DQ9 – DQ17 (the upper bits).

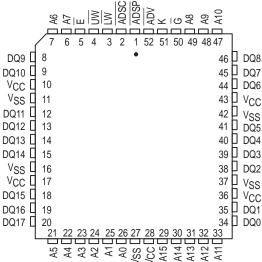
This device is ideally suited for systems that require wide data bus widths and cache memory. See Figure 2 for applications information.

- Single 5 V ±5% Power Supply
- Fast Access Time: 9 ns Max
- Byte Writeable via Dual Write Enables
- · Internal Input Registers (Address, Data, Control)
- Internally Self-Timed Write Cycle
- ADSP, ADSC, and ADV Burst Control Pins
- · Asynchronous Output Enable Controlled Three-State Outputs
- Common Data Inputs and Data Outputs
- 3.3 V I/O Compatible
- High Board Density 52-Lead PLCC Package

MCM67B618B



PIN ASSIGNMENTS



A0 - A15 Address Inputs K Clock ADV Burst Address Advance LW Lower Byte Write Enable UW Upper Byte Write Enable ADSC Controller Address Status ADSP Processor Address Status E Chip Enable G Output Enable
DQ0 – DQ17 Data Input/Output
VCC · · · · · +5 V Power Supply
VSS Ground NC No Connection

All power supply and ground pins must be connected for proper operation of the device.

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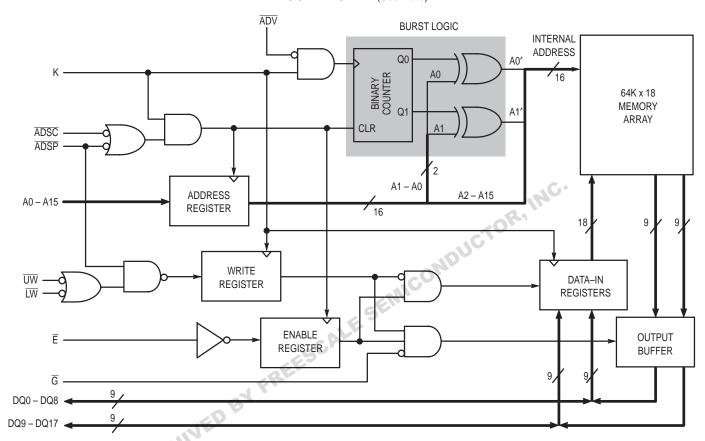
This document contains information on a new product. Specifications and information herein are subject to change without notice.

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BLOCK DIAGRAM (See Note)



NOTE: All registers are positive—edge triggered. The ADSC or ADSP signals control the duration of the burst and the start of the next burst. When ADSP is sampled low, any ongoing burst is interrupted and a read (independent of W and ADSC) is performed using the new external address. Alternatively, an ADSP—initiated two cycle WRITE can be performed by asserting ADSP and a valid address on the first cycle, then negating both ADSP and ADSC and asserting LW and/or UW with valid data on the second cycle (see Single Write Cycle in WRITE CYCLES timing diagram).

When \overline{ADSC} is sampled low (and \overline{ADSP} is sampled high), any ongoing burst is interrupted and a read or write (dependent on \overline{W}) is performed using the new external address. Chip enable (\overline{E}) is sampled only when a new base address is loaded. After the first cycle of the burst, \overline{ADV} controls subsequent burst cycles. When \overline{ADV} is sampled low, the internal address is advanced prior to the operation. When \overline{ADV} is sampled high, the internal address is not advanced, thus inserting a wait state into the burst sequence accesses. Upon completion of a burst, the address will wrap around to its initial state. See **BURST SEQUENCE TABLE**. Write refers to either or both byte write enables (\overline{LW} , \overline{UW}).

BURST SEQUENCE TABLE (See Note)

External Address 1st Burst Address 2nd Burst Address 3rd Burst Address

A15 – A2	A1	A0
A15 – A2	A1	A0
A15 – A2	A1	A0
A15 – A2	A1	A0

NOTE: The burst wraps around to its initial state upon completion.



SYNCHRONOUS TRUTH TABLE (See Notes 1, 2, and 3)

Ē	ADSP	ADSC	ADV	UW or LW	K	Address Used	Operation
Н	L	Х	Х	Х	L–H	N/A	Deselected
Н	Х	L	Х	Х	L–H	N/A	Deselected
L	L	Х	Х	Х	L–H	External Address	Read Cycle, Begin Burst
L	Н	L	Х	L	L–H	External Address	Write Cycle, Begin Burst
L	Н	L	Х	Н	L–H	External Address	Read Cycle, Begin Burst
Х	Н	Н	L	L	L–H	Next Address	Write Cycle, Continue Burst
Х	Н	Н	L	Н	L–H	Next Address	Read Cycle, Continue Burst
Х	Н	Н	Н	L	L–H	Current Address	Write Cycle, Suspend Burst
Х	Н	Н	Н	Н	L–H	Current Address	Read Cycle, Suspend Burst

NOTES:

- 2. All inputs except \overline{G} must meet setup and hold times for the low–to–high transition of clock (K).

 3. Wait states are inserted by suspending burst.

ASYNCHRONOUS TRUTH TABLE (See Notes 1 and 2)

Wait states are inserted by suspending burst.							
ASYNCHRONOUS TRUTH TABLE (See Notes 1 and 2)							
Operation	G	I/O Status					
Read	L	Data Out					
Read	Н	High–Z					
Write	Х	High–Z — Data In					
Deselected	Х	High–Z					

NOTES:

- 1. X means Don't Care.
- 2. For a write operation following a read operation, \overline{G} must be high before the input data required setup time and held high through the input data hold time.

ABSOLUTE MAXIMUM RATINGS (Voltages Referenced to VSS = 0 V)

Rating	Symbol	Value	Unit
Power Supply Voltage	Vcc	-0.5 to 7.0	V
Voltage Relative to VSS for Any Pin Except VCC	V _{in} , V _{out}	-0.5 to V _{CC} + 0.5	V
Output Current (per I/O)	l _{out}	±30	mA
Power Dissipation	PD	1.6	W
Temperature Under Bias	T _{bias}	-10 to 85	°C
Ambient Temperature	TA	0 to 70	°C
Storage Temperature	T _{stg}	-55 to 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established.

This device contains circuitry that will ensure the output devices are in High-Z at



DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 5.0 \text{ V} \pm 5\%, T_A = 0^{\circ} \text{ to } 70^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

RECOMMENDED OPERATING CONDITIONS (Voltages Referenced to V_{SS} = 0 V)

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	Vcc	4.75	5.25	V
Input High Voltage	VIH	2.2	V _{CC} + 0.3**	V
Input Low Voltage	V _{IL}	-0.5*	0.8	V

^{*} V_{IL} (min) = -0.5 V dc; V_{IL} (min) = -2.0 V ac (pulse width ≤ 20.0 ns) for $I \leq 20.0$ mA.

DC CHARACTERISTICS AND SUPPLY CURRENTS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V _{in} = 0 to V _{CC})	l _{lkg(l)}		±1.0	μΑ
Output Leakage Current (G = V _{IH})	llkg(O)	_	±1.0	μΑ
AC Supply Current (Device Selected, All Outputs Open, Freq = Max)	ICCA	_	275	mA
CMOS Standby Supply Current (Device Deselected, Freq = 0, V_{CC} = Max, All Inputs Static at CMOS Levels $V_{in} \le V_{SS}$ + 0.2 V or $\ge V_{CC}$ – 0.2 V)	I _{SB1}	_	95	mA
Output Low Voltage (I _{OL} = 8.0 mA)	VOL	_	0.4	V
Output High Voltage (I _{OH} = -4.0 mA)	VOH	2.4	3.3	V

NOTE: Good decoupling of the local power supply should always be used. DC characteristics are guaranteed for all possible i486 and Pentium bus cycles.

$\textbf{CAPACITANCE} \text{ (f = 1.0 MHz, T}_{A} = 25^{\circ}\text{C, Periodically Sampled Rather Than 100\% Tested)}$

Parameter	Symbol	Тур	Max	Unit
Input Capacitance	C _{in}	4	5	pF
Input/Output Capacitance	C _{I/O}	6	8	pF

^{**} V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2.0 V ac (pulse width \leq 20.0 ns) for $I \leq$ 20.0 mA.



AC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 5.0 \text{ V} \pm 5\%, T_A = 0^{\circ} \text{ to } 70^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

Input Timing Measurement Reference Level 1.5 V	Output Timing Reference Level 1.5 V
Input Pulse Levels 0 to 3.0 V	Output Load See Figure 1 Unless Otherwise Noted
Input Rise/Fall Time 3 ns	

READ/WRITE CYCLE TIMING (See Notes 1, 2, and 3)

		MCM67E	3618B-9		
Parameter	Symbol	Min	Max	Unit	Notes
Cycle Time	^t KHKH	15	_	ns	
Clock Access Time	^t KHQV	_	9	ns	4
Output Enable to Output Valid	^t GLQV	_	5	ns	
Clock High to Output Active	^t KHQX1	6	_	ns	
Clock High to Output Change	^t KHQX2	3	_	ns	
Output Enable to Output Active	tGLQX	0	_	ns	
Output Disable to Q High–Z	^t GHQZ	_	6	ns	5
Clock High to Q High-Z	^t KHQZ	3	6	ns	
Clock High Pulse Width	^t KHKL	5	_	ns	
Clock Low Pulse Width	^t KLKH	5	_	ns	
Setup Times: Address Status Data In Write Address Advance Chip Enable	[†] AVKH [†] ADSVKH [†] DVKH [†] WVKH [†] ADVVKH [†] EVKH	2.5	_	ns	6
Hold Times: Address Address Status Data In Write Address Advance Chip Enable	tKHAX tKHADSX tKHDX tKHWX tKHADVX tKHADVX	0.5	_	ns	6

NOTES:

- 1. In setup and hold times, W (write) refers to either one or both byte write enables \overline{LW} and \overline{UW} .
- 2. All read and write cycle timings are referenced from K or \overline{G} .
- 3. \overline{G} is a don't care when \overline{UW} or \overline{LW} is sampled low.
- 4. Maximum access times are guaranteed for all possible i486 and Pentium external bus cycles.
- 5. Transition is measured ±500 mV from steady–state voltage. This parameter is sampled rather than 100% tested. At any given voltage and temperature, tkHQZ max is less than tkHQZ1 min for a given device and from device to device.
- 6. This is a synchronous device. All addresses must meet the specified setup and hold times for *ALL* rising edges of K whenever ADSP or ADSC is low, and the chip is selected. All other synchronous inputs must meet the specified setup and hold times for *ALL* rising edges of K when the chip is enabled. Chip enable must be valid at each rising edge of clock for the device (when ADSP or ADSC is low) to remain enabled.

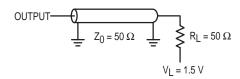
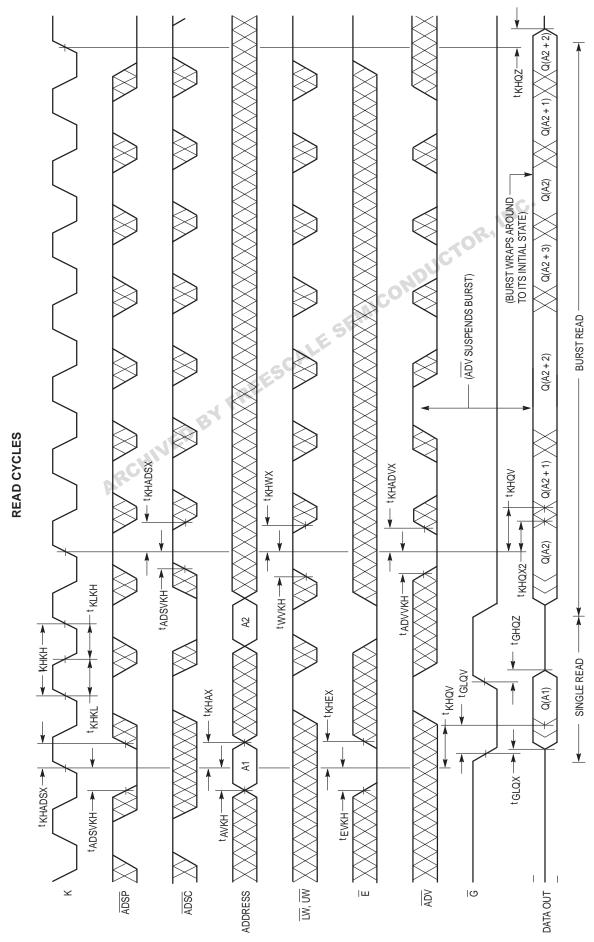


Figure 1. Test Load



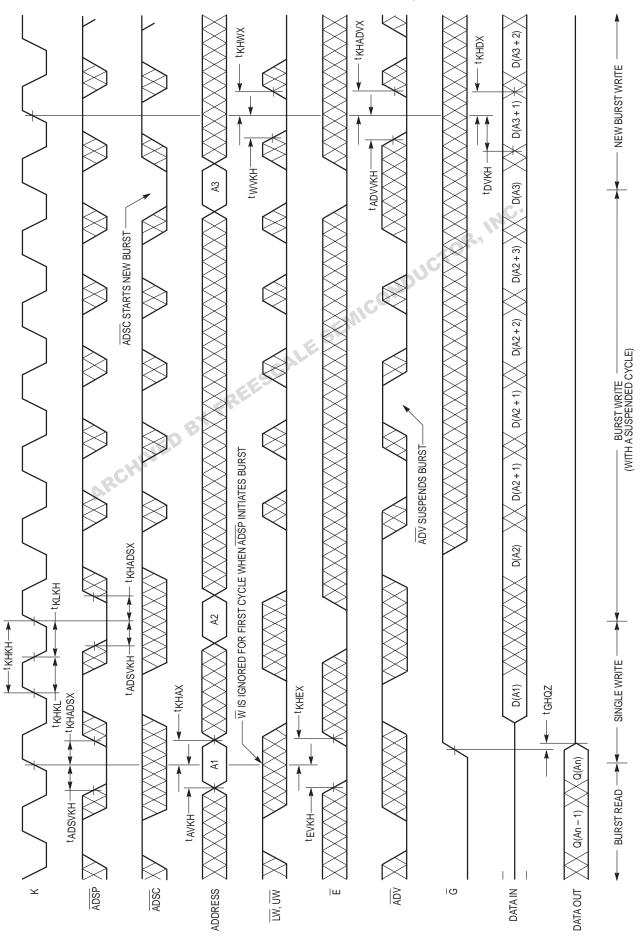


NOTE: Q(A2) represents the first output data from the base address A2; Q(A2 + 1) represents the next output data in the burst sequence with A2 as the base address.

WRITE CYCLES

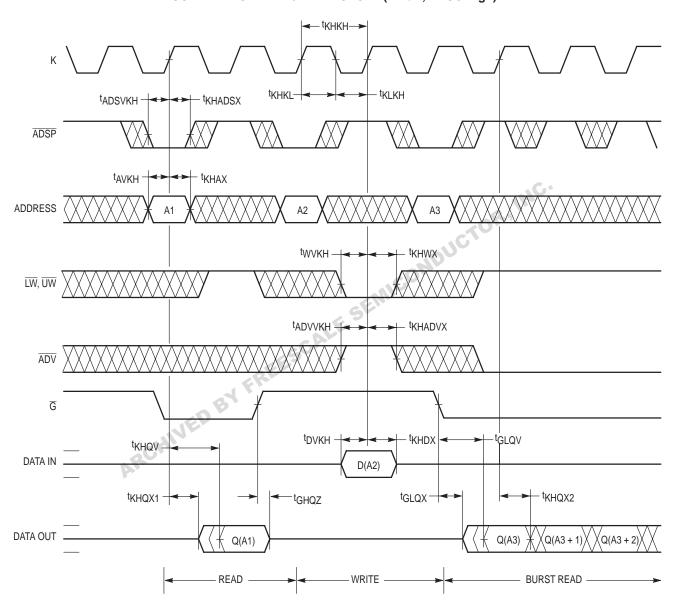


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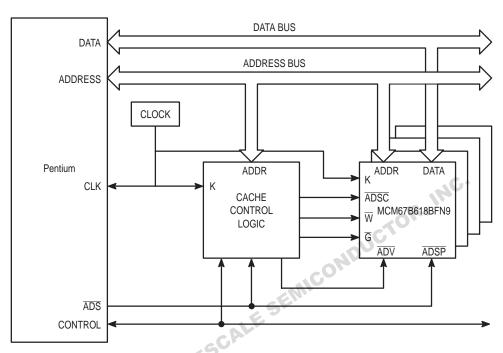


COMBINATION READ/WRITE CYCLE (E Low, ADSC High)





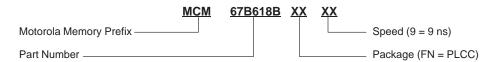
APPLICATION EXAMPLE



512K Byte Burstable, Secondary Cache Using Four MCM67B618BFN9s with a 66 MHz Pentium ARCHIVED BY

Figure 2

ORDERING INFORMATION (Order by Full Part Number)

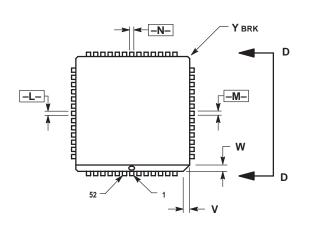


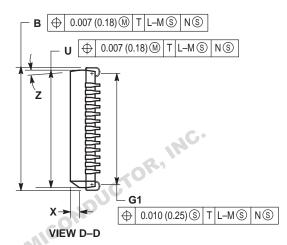
Full Part Number — MCM67B618BFN9

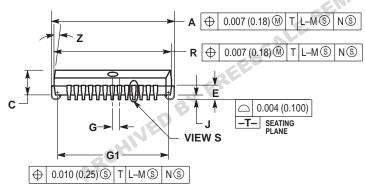


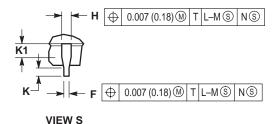
PACKAGE DIMENSIONS

FN PACKAGE 52-LEAD PLCC **CASE 778-02**









- NOTES:

 1. DATUMS -L-, -M-, AND -N- DETERMINED WHERE TOP OF LEAD SHOULDER EXITS PLASTIC BODY AT MOLD PARTING LINE.
- 2. DIMENSION G1, TRUE POSITION TO BE MEASURED AT DATUM -T-, SEATING PLANE.

 3. DIMENSIONS R AND U DO NOT INCLUDE MOLD
- FLASH. ALLOWABLE MOLD FLASH IS 0.010 (0.250) PER SIDE.
- 4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

INCHES

- 5. CONTROLLING DIMENSION: INCH.
 6. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM BY UP TO 0.012 (0.300).
 DIMENSIONS R AND U ARE DETERMINED AT THE
 OUTERMOST EXTREMES OF THE PLASTIC BODY
 EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
- OF THE PLASTIC BODY.

 7. DIMENSION H DOES NOT INCLUDE DAMBAR
 PROTRUSION OR INTRUSION. THE DAMBAR
 PROTRUSION(S) SHALL NOT CAUSE THE H
 DIMENSION TO BE GREATER THAN 0.037 (0.940). THE DAMBAR INTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE SMALLER THAN 0.025 (0.635).

MILLIMETERS

	INCHES		IVIILLIIV	ILIEKS	
DIM	MIN	MAX	MIN	MAX	
Α	0.785	0.795	19.94	20.19	
В	0.785	0.795	19.94	20.19	
С	0.165	0.180	4.20	4.57	
Е	0.090	0.110	2.29	2.79	
F	0.013	0.019	0.33	0.48	
G	0.050	BSC	1.27	BSC	
Н	0.026	0.032	0.66	0.81	
J	0.020		0.51		
K	0.025		0.64		
R	0.750	0.756	19.05	19.20	
U	0.750	0.756	19.05	19.20	
٧	0.042	0.048	1.07	1.21	
W	0.042	0.048	1.07	1.21	
Х	0.042	0.056	1.07	1.42	
Υ		0.020	_	0.50	
Z	2°	10°	2°	10°	
G1	0.710	0.730	18.04	18.54	
K1	0.040		1.02		



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